Photothermoelectric p-n Junction Photodetectors Based on Macroscopic Films of Aligned Carbon Nanotubes in the Terahertz Range

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Terahertz (THz) technologies are quickly developing for non-invasive sensing, characterization, and communication applications. Lasers and modulators in this region have been studied extensively though THz detection systems remain relatively unexplored. Carbon nanotubes (CNTs) exhibit strong absorption in the THz, making them promising for THz detection. Studies in the ultraviolet (UV) to near-infrared (NIR) have demonstrated CNTs' capability of absorbing light via interband transitions, whose excitonic origin and diameter/chirality dependence basically are well understood. The origin of THz absorption in CNTs is relatively unclear, remains rather controversial, though promising for detection applications. Here we investigate photothermoelectric p-n junction photodetectors based on macroscopic films of aligned CNTs [1]. CNTs were grown via chemical vapor deposition and rolled down, creating horizontally-aligned films, then transferred to substrates. Two films were used in device fabrication. One was unintentionally p-doped by atmospheric molecules, while the other was n-doped using benzyl viologen and placed over the p-doped film, creating a p-n junction. Two electrodes contacted each side, allowing the voltage across to be measured. A broadband photoresponse was previously found in these devices in the UV to NIR [1]. We aim to further characterize these devices' functionality in the THz range. Our setup consists a CO₂ laser that pumps a far-infrared molecular gas laser, which emits various THz wavelengths. The beam was focused on the sample's p-n junction. From previous experiments, we know this junction is significantly the most responsive area. We will discuss our results as a function of THz laser power, polarization, and wavelength.

[1] Xiaowei He, Xuan Wang, Sébastien Nanot, *et al.*, "Photothermoelectric p–n Junction Photodetector with Intrinsic Broadband Polarimetry Based on Macroscopic Carbon Nanotube Films," *ACS Nano*, published online on June 30, 2013. DOI: 10.1021/nn402679u.

Films of Aligned Carbon Nanotubes in the Terahertz Range

Material & Device History

Previous carbon nanotube

- ~ 4 Terahertz (THz) [1]



and polarization dependences.



